

Silicon PNP Power Transistors 2N5605 2N5607 2N5609 2N5611

DESCRIPTION

- With TO-66 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For general-purpose amplifier ;
and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5605	Open emitter	-80	V
		2N5607/5609		-100	
		2N5611		-120	
V_{CEO}	Collector-emitter voltage	2N5605	Open base	-60	V
		2N5607/5609		-80	
		2N5611		-100	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-5	A
P_D	Total power dissipation		$T_C=25$	25	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	4.37	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	2N5605	I _C =50mA ; I _B =0	-60			V
		2N5607/5609		-80			
		2N5611		-100			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-1A; I _B =-0.1A			-0.5	V
V _{BE}	Base-emitter on voltage		I _C =-2.5A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =Rated V _{CBO} ; I _E =0			-0.1	mA
I _{CEO}	Collector cut-off current		V _{CE} = Rated V _{CEO} , I _B =0			-1.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE}	DC current gain	2N5605/5609	I _C =-2.5A ; V _{CE} =-5V	70		200	
		2N5607/5611		30		90	
f _T	Transition frequency	2N5605/5609	I _C =-0.5A ; V _{CE} =-10V	70			MHz
		2N5607/5611		60			

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PACKAGE OUTLINE

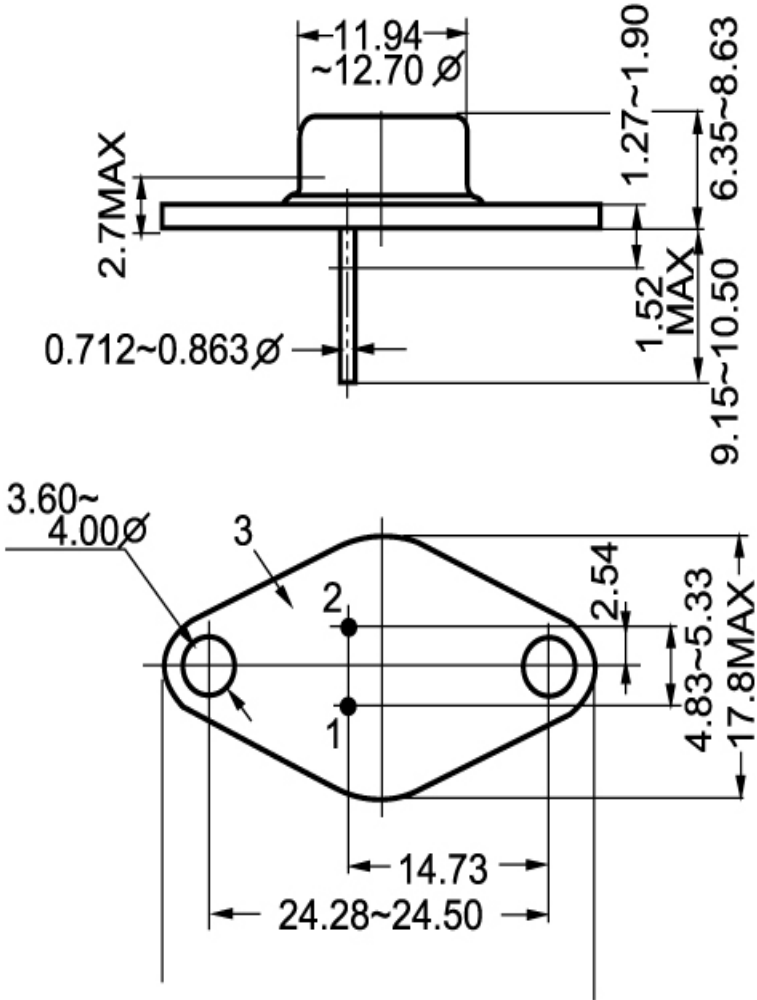


Fig.2 outline dimensions